

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): M.A. Shibib et al.

Case: 41-10

Serial No.: To Be Assigned

Filing Date: November 21, 2003

Group: To Be Assigned

Examiner: To Be Assigned

Title: Metal-Oxide-Semiconductor Device  
Formed in Silicon-On-Insulator

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**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants' attorney wishes to bring to the attention of the Patent and Trademark Office the following documents listed on the accompanying Form PTO-1449. A copy of each listed document is enclosed, other than the published U.S. patent document.

**U.S. Patent Documents**

1. U.S. Patent No. 6,461,902 issued on 10/08/02 to Xu et al.

**Other Documents**

1. J. Cai et al., "A Partial SOI Technology for Single-Chip RF Power Amplifiers," IEEE, pp. 40.3.1-40.3.4, 2001.
2. S. Matsumoto et al., "A Quasi-SOI Power MOSFET for Radio Frequency Applications Formed by Reversed Silicon Wafer Direct Bonding," IEEE, pp. 1448-1453, 2001.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability, or as a representation that no other material information exists.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Wayne L. Ellenbogen", with a long, sweeping horizontal line extending to the right.

Date: November 21, 2003

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**FORM PTO-1449 (MODIFIED)****LIST OF PUBLICATIONS FOR  
APPLICANT'S INFORMATION  
DISCLOSURE STATEMENT**

Applicant(s): M.A. Shbib et al.  
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**U.S. PATENT DOCUMENTS**

EXAMINER				FILING DATE
INITIAL	DOCUMENT NO.	DATE	NAME	IF APPROPRIATE

1.	6,461,902	10/08/02	Xu et al.	
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**FOREIGN PATENT DOCUMENTS**

EXAMINER				TRANSLATION	
INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	YES NO

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**OTHER DOCUMENTS**

EXAMINER		
INITIAL	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.

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| 1. | J. Cai et al., "A Partial SOI Technology for Single-Chip RF Power Amplifiers," IEEE, pp. 40.3.1-40.3.4, 2001.  |
| 2. | S. Matsumoto et al., "A Quasi-SOI Power MOSFET for Radio Frequency Applications Formed by Reversed Silicon Wafer Direct Bonding," IEEE, pp. 1448-1453, 2001. |

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Examiner

Date Considered

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**Examiner:** Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.